

REMARKS

In response to the Official Action mailed September 8, 2003, Applicants amend their application and request reconsideration. No claims are added or cancelled so that claims 13-16 remain pending.

The Examiner pointed out an apparent error in the specification at page 7. That error is corrected. In the course of correcting that error, the paragraph including the error is revised for easier understanding, but without a change in content.

In this Amendment the two pending independent claims, claims 13 and 15, are clarified. Those claims incorrectly stated that the open stub capacitance employs the dielectric film that both surrounds and affects the capacitance of the transistor and that provides the dielectric film of the MIM capacitor. This statement within the claims was incorrect. The only change made here to the claims is withdrawal of that incorrect description.

With respect to the embodiment of the invention shown in Figure 1, the corresponding Smith chart is shown in Figure 3. The points at which the gate-source capacitance of the transistor 26 is viewed, points a, b, c, and d, are plotted on this Smith chart of Figure 3 and given corresponding reference letters. It is well known by those of skill in the art that the object of impedance matching is achieved when the impedance falls at the center of the Smith chart, for example point d in Figure 3. The Smith chart of Figure 3 illustrates that as the capacitance is viewed sequentially from point a to point d the impedance changes, and the open stub capacitance, represented by L1 in the embodiment of Figure 1, results in achieving the desired input impedance exact matching at the input point 5. A similar Smith chart is illustrated in Figure 5 for the embodiment of the invention illustrated in Figure 6, showing the same result with respect to an output impedance. The point of the invention is that by employing the same dielectric film with regard to the transistor and the MIM capacitor, there are offsetting changes in capacitances due to variations in the thickness of the film. By further adding the open stub capacitance, the desired exact impedance match is achieved.

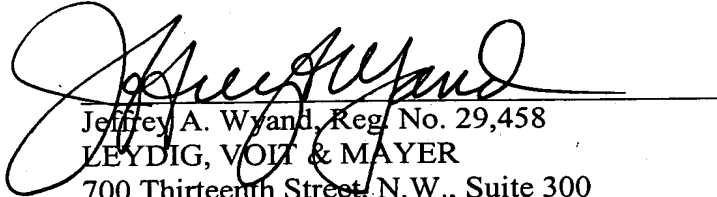
No claim has been examined on the merits in the lengthy and complex prosecution of this patent application. In the Office Action mailed September 8, claims 13-16 were rejected pursuant to 35 USC 112, first paragraph because of the incorrect limitation in claims 13 and 15 concerning the incorporation of the insulating films dielectric in the open stub capacitance. In view of the withdrawal of that description in those two claims, the claims now pending are in form for allowance or, alternatively, examination on the merits. If there is an examination and a

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prior art rejection, Applicants respectfully request, in view of the complex prosecution history of this patent application, that any prior rejection not be a final rejection.

Prompt and favorable action on the merits is earnestly solicited.

Respectfully submitted,



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JAW/tps

Amendment or ROA - Regular (Revised 9/03/03)